

CORRECTION

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Correction: A non-volatile resistive memory effect in 2,2',6,6'-tetraphenyl-dipyranylidene thin films as observed in field-effect transistors and by conductive atomic force microscopy

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The authors regret that the name of the sixth author was presented incorrectly in the original article. Subodh G. Mhaisalkar's name has been corrected herein.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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